DU1215S



RF Power MOSFET Transistor 15W, 2-175MHz, 12V

M/A-COM Products Released; RoHS Compliant

Features

- N-Channel enhancement mode device
- DMOS structure
- Lower capacitances for broadband operation
- High saturated output power
- Lower noise figure than bipolar devices
- Specifically designed for 12 volt applications

ABSOLUTE MAXIMUM RATINGS AT 25° C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	20	V
Drain-Source Current	I _{DS}	4	Α
Power Dissipation	P_D	87.5	W
Junction Temperature	T_J	200	°C
Storage Temperature	T _{STG}	-55 to +150	°C
Thermal Resistance	θ_{JC}	2	°C/W

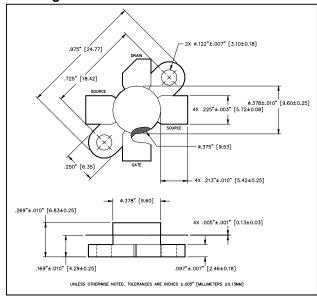
TYPICAL DEVICE IMPEDANCE

F (MHz)	Z _{IN} (Ω)	Z _{LOAD} (Ω)		
30	3.0 - j25	4.0 - j3.0		
100	3.0 - j15	3.5 - j1.5		
175	5.0 - j8 4.0 - j0.0			
$V_{DD} = 12V$, $I_{DQ} = 100$ mA, $P_{OUT} = 15$ W				

Z_{IN} is the series equivalent input impedance of the device from gate to source.

Z_{LOAD} is the optimum series equivalent load impedance as measured from drain to ground.

Package Outline



LETTER	MILLIM	ETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	24.64	24.89	.970	.980
В	18.29	18.54	.720	.730
С	20.07 20.83		.790	.820
D	9.47	9.73	.373	.383
E	6.22	6.48	.245	.255
F	5.64	5.79	.222	.228
G	2.92	3.30	.115	.130
Н	2.29	2.67	.090	.105
J	4.04	4.55	.159	.179
К	6.58	7.39	.259	.291
L	.10	.15	.004	.006

ELECTRICAL CHARACTERISTICS AT 25°C

Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	40	-	V	$V_{GS} = 0.0 \text{ V}$, $I_{DS} = 5.0 \text{ mA}$
Drain-Source Leakage Current	I _{DSS}	-	1.0	mA	V _{GS} = 15.0 V , V _{GS} = 0.0 V
Gate-Source Leakage Current	I _{GSS}	-	1.0	μA	V _{GS} = 20.0 V , V _{DS} = 0.0 V
Gate Threshold Voltage	$V_{GS(TH)}$	20	6.0	V	V _{DS} = 10.0 V , I _{DS} = 100 mA
Forward Transconductance	G _M	0.5	-	S	V_{DS} = 10.0 V , I_{DS} = 1000 mA , Δ V_{GS} = 1.0 V
Input Capacitance	C _{ISS}	-	50	pF	V _{DS} = 12.0 V , F = 1.0 MHz
Output Capacitance	Coss	-	60	pF	V _{DS} = 12.0 V , F = 1.0 MHz
Reverse Capacitance	C _{RSS}	-	12	pF	V _{DS} = 12.0 V , F = 1.0 MHz
Power Gain	G _P	9.5	-	dB	V _{DD} = 12.0 V, I _{DQ} = 100 mA, P _{OUT} = 15 W F =175 MHz
Drain Efficiency	ŋ₀	60	-	%	V _{DD} = 12.0 V, I _{DQ} = 100 mA, P _{OUT} = 15 W F =175 MHz
Load Mismatch	VSWR-T	-	30:1	-	V _{DD} = 12.0 V, I _{DQ} = 100 mA, P _{OUT} = 15 W F =175 MHz

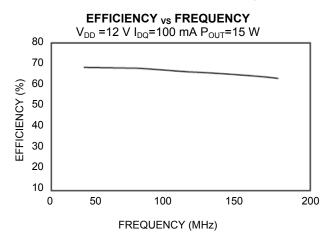
- North America Tel: 800.366.2266 / Fax: 978.366.2266
- Europe Tel: 44.1908.574.200 / Fax: 44.1908.574.300
- Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298 Visit www.macomtech.com for additional data sheets and product information.

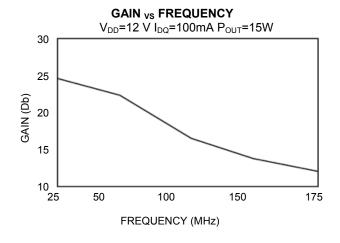


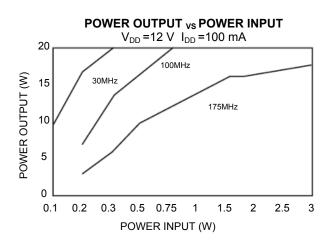
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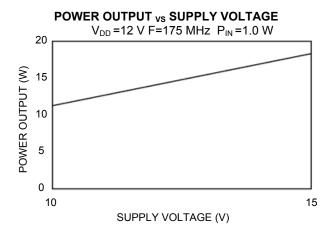
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Typical Broadband Performance Curves









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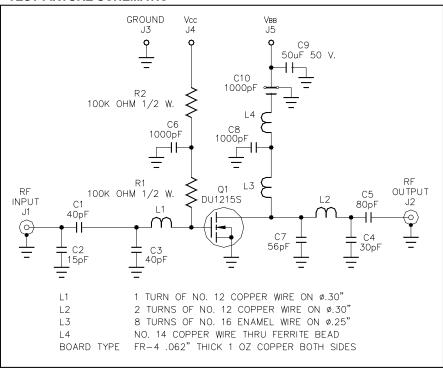
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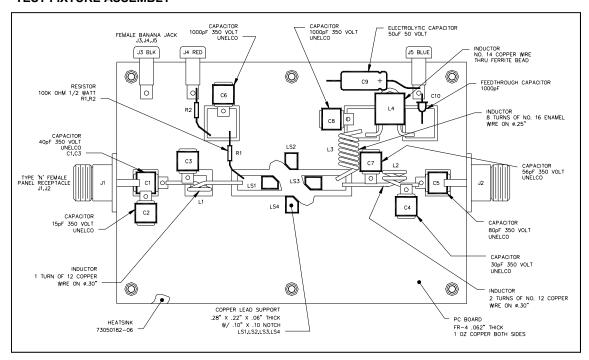
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TEST FIXTURE SCHEMATIC



TEST FIXTURE ASSEMBLY



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